

CMXD2004

**SURFACE MOUNT
TRIPLE ISOLATED
HIGH VOLTAGE
SILICON SWITCHING DIODES**

SUPERmini™



SOT-26 CASE



www.centrasemi.com

DESCRIPTION:

The CENTRAL SEMICONDUCTOR CMXD2004 type contains three (3) Isolated High Voltage Silicon Switching Diodes, manufactured by the epitaxial planar process, epoxy molded in a SUPERmini™ surface mount package, designed for applications requiring high voltage capability.

MARKING CODE: X04

MAXIMUM RATINGS: ($T_A=25^{\circ}\text{C}$)

Continuous Reverse Voltage
Peak Repetitive Reverse Voltage
Average Forward Current
Continuous Forward Current
Peak Repetitive Forward Current
Peak Forward Surge Current, $t_p=1.0\mu\text{s}$
Peak Forward Surge Current, $t_p=1.0\text{s}$
Power Dissipation
Operating and Storage Junction Temperature
Thermal Resistance

SYMBOL

V_R 240
 V_{RRM} 300
 I_O 200
 I_F 225
 I_{FRM} 625
 I_{FSM} 4.0
 I_{FSM} 1.0
 P_D 350
 T_J, T_{stg} -65 to +150
 Θ_{JA} 357

UNITS

V
V
mA
mA
mA
A
A
mW
 $^{\circ}\text{C}$
 $^{\circ}\text{C/W}$

ELECTRICAL CHARACTERISTICS PER DIODE: ($T_A=25^{\circ}\text{C}$ unless otherwise noted)

SYMBOL	TEST CONDITIONS	MIN	MAX	UNIT
I_R	$V_R=240\text{V}$		100	nA
I_R	$V_R=240\text{V}, T_A=150^{\circ}\text{C}$		100	μA
BV_R	$I_R=100\mu\text{A}$	300		V
V_F	$I_F=100\text{mA}$		1.0	V
C_T	$V_R=0, f=1.0\text{MHz}$		5.0	pF
t_{rr}	$I_F=I_R=30\text{mA}, I_{rr}=3.0\text{mA}, R_L=100\Omega$		50	ns

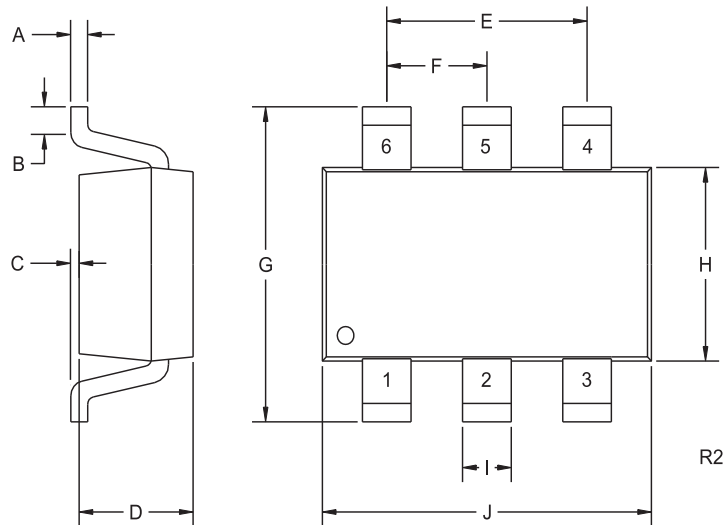
R4 (9-February 2010)

CMXD2004

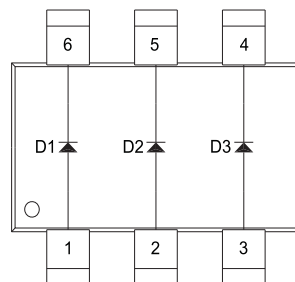
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SOT-26 CASE - MECHANICAL OUTLINE



PIN CONFIGURATION



SYMBOL	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.004	0.007	0.11	0.19
B	0.016	-	0.40	-
C	-	0.004	-	0.10
D	0.039	0.047	1.00	1.20
E	0.074	0.075	1.88	1.92
F	0.037	0.038	0.93	0.97
G	0.102	0.118	2.60	3.00
H	0.059	0.067	1.50	1.70
I	0.016		0.41	
J	0.110	0.118	2.80	3.00

SOT-26 (REV: R2)

LEAD CODE:

- 1) Anode D1
- 2) Anode D2
- 3) Anode D3
- 4) Cathode D3
- 5) Cathode D2
- 6) Cathode D1

MARKING CODE: X04

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